

Title (en)

APPARATUS AND METHOD FOR FORMING A MEMBRANE WITH NANOMETER SCALE PORES

Title (de)

APPARAT UND VERFAHREN FÜR DIE HERSTELLUNG EINER MEMBRAN MIT POREN IM NANOMETERBEREICH

Title (fr)

APPAREIL ET PROCEDE DE FORMATION D'UNE MEMBRANE A PORES A L'ECHELLE NANOMETRIQUE

Publication

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Application

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Priority

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Abstract (en)

[origin: WO0136321A1] A method of forming a membrane with nanometer scale pores includes forming a sacrificial etch stop layer on a substrate. A base layer is constructed on the sacrificial etch stop layer. Micrometer scale pores are formed within the base layer. A sacrificial base layer is built on the base layer. The sacrificial base layer is removed from selected regions of the base layer to define nanometer scale pores within the base layer. The resultant membrane has sub-fifty nanometer pores formed within it.

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